

1000V 8A N-channel Enhancement Mode Power MOSFET

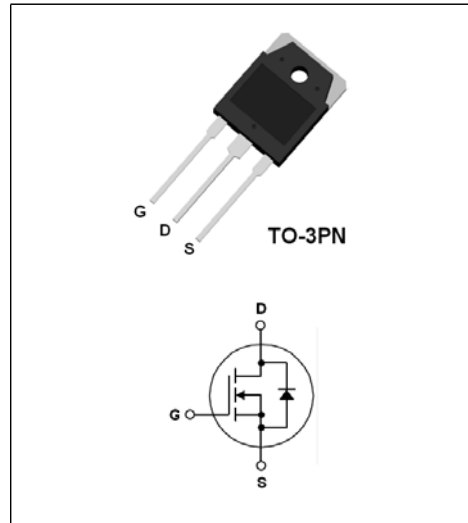
Description

The AKT8N100NB is an N-Channel enhancement mode power MOSFET which using proprietary planar stripe and DMOS technology.

This MOSFET has low static on-resistance and high avalanche energy strength. This device provide excellent switching performance for Switched Mode Power Supplies, Electronic Ballast and Electronic Transformer.

Features

- Low on-Resistance: $R_{DS(on)}=1.30\Omega(\text{typ.})$
- Special Process Technology for high ESD Capability
- 100% Avalanche Test
- Good Stability and Uniformity with High E_{AS}
- RoHS Compliant



Applications

Switched Mode Power Supplies

Electronic Ballast And Electronic Transformer

Absolute Maximum Ratings @ $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain to Source Voltage	1000	V
V_{GSS}	Gate to Source Voltage	± 30	V
I_D	Drain Current	$T_C=25^\circ\text{C}$	8
		$T_C=100^\circ\text{C}$	5.1
I_{DM}	Pulsed Drain Current (Note1)	36	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	280
	Derate above 25°C		2.22
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	600	mJ
T_J	Operating Junction Temperature Range	-55~+150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55~+150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$	Thermal Resistance, Junction to case	0.45	$^\circ\text{C}/\text{W}$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics @T_C=25 °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	1000	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	3.0	3.65	5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =4.0A	-	1.30	1.50	Ω
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =1000V, V _{GS} =0V	-	-	10	uA
I _{GSS}	Gate to Source Leakage Current	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA

D-S Diode Characteristics and Maximum Rating @T_C=25 °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Maximum Drain to Source Diode Forward Current		-	-	9	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =8A	-	0.84	1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =8A,	-	0.5	-	us
Q _{rr}	Reverse Recovery Charge	di/dt=-100A/us	-	6.4	-	uC

Switching Characteristics @T_C=25 °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on Delay Time	I _D =8A, V _{DD} =500V, R _G =25Ω (Note 3)	-	50	105	ns
t _r	Rising Time		-	114	245	ns
t _{d(off)}	Turn-off Delay Time		-	92	200	ns
t _f	Falling Time		-	75	155	ns
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1.0MHz	-	-	2720	pF
C _{oss}	Output Capacitance		-	-	220	pF
C _{rss}	Reverse Transfer Capacitance		-	-	18	pF
Q _g	Total Gate Charge	I _D =8A, V _{DS} =720V V _{GS} =10V (Note 3)	-	43	-	nC
Q _{gs}	Gate to Source Charge		-	11	-	nC
Q _{gd}	Gate to Drain Charge		-	16	-	nC

Note:

1. Repetitive rating: pulse-width limited by maximum junction temperature
2. L=10mH, V_{DD}=100V, V_G=10V, @T_C=25°C
3. Essentially independent of operating temperature typical characteristics

Typical Performance Characteristics

Fig. 1. Typical on-Region Characteristics

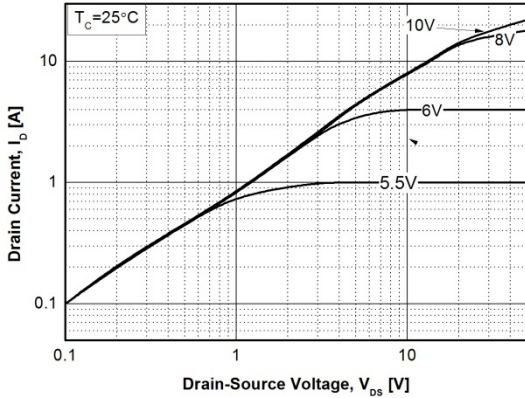


Fig. 2. Typical Transfer Characteristics

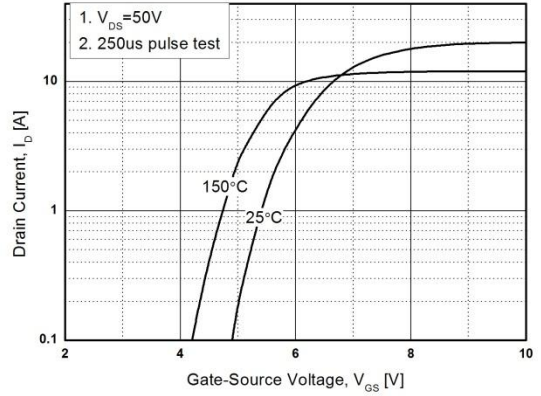


Fig. 3. Static on-Resistance vs. I_D

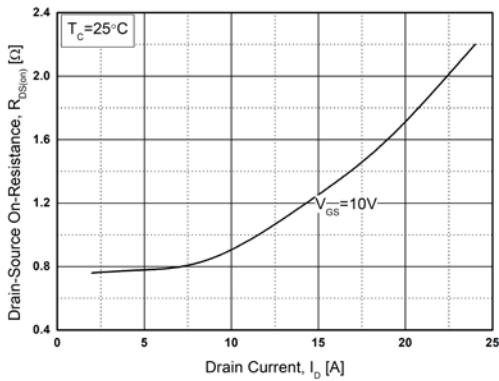


Fig. 4. Body Diode Forward Voltage vs. I_{DR}

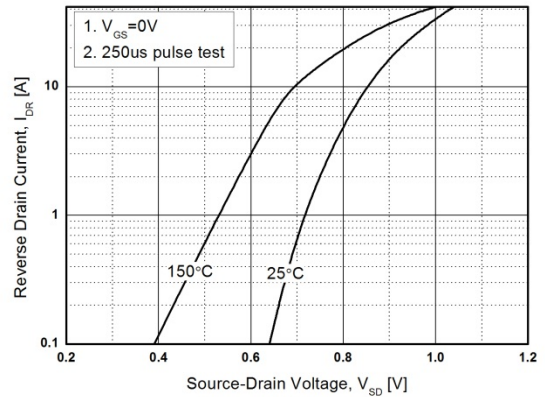


Fig. 5. Capacitance Characteristics

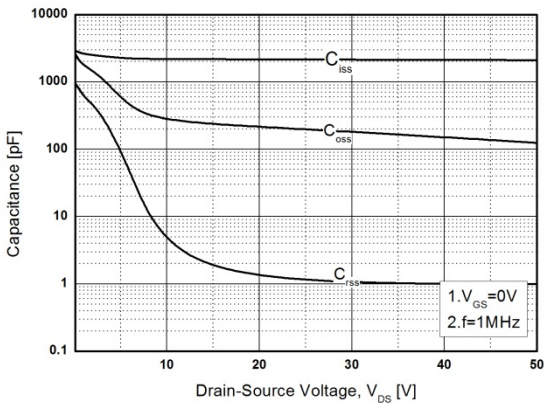
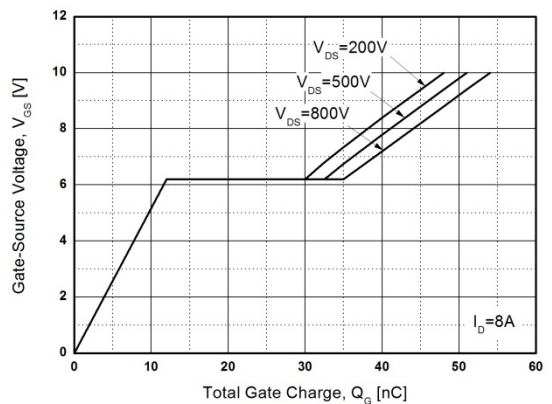


Fig. 6. Gate Charge Characteristics



Typical Performance Characteristics

Fig. 7. Breakdown Voltage vs. Temperature

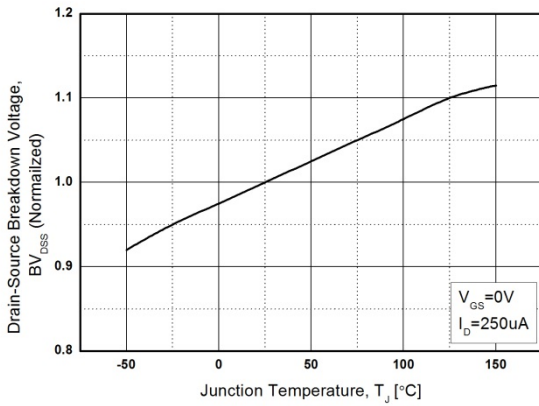


Fig. 8. Static on-Resistance vs. Temperature

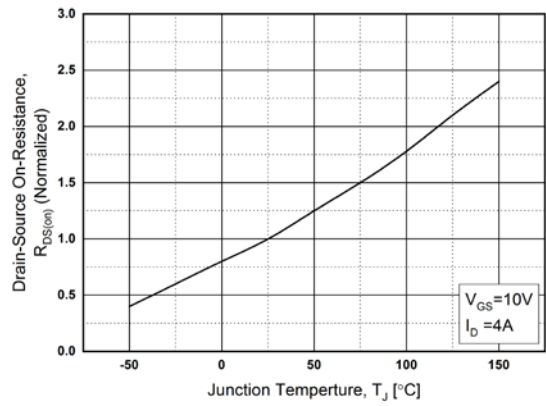


Fig. 9. Maximum Safe Operating Area

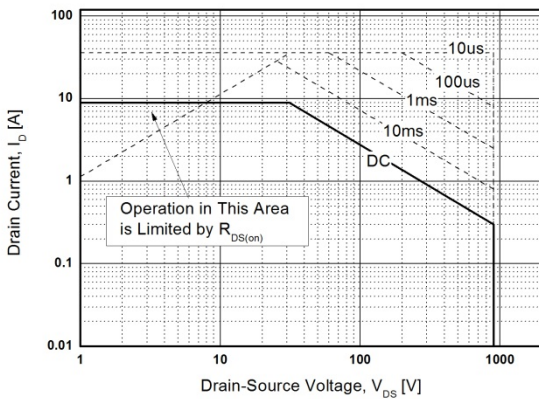


Fig. 10. Maximum Drain Current vs. Temperature

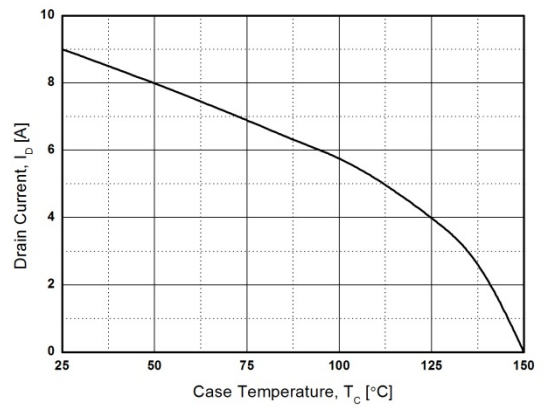
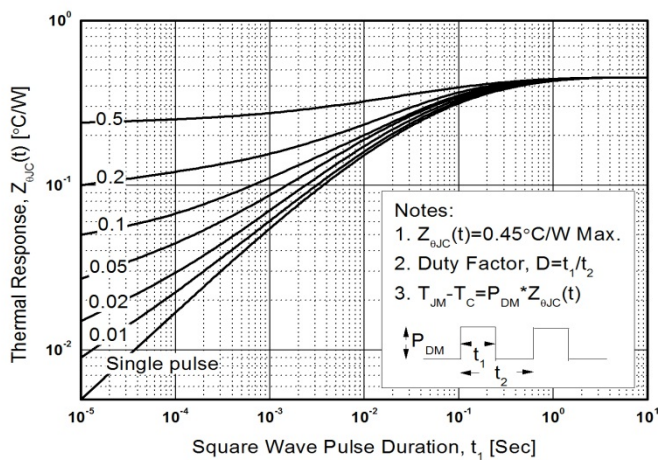


Fig. 11. Transient Thermal Response Curve



Package Dimensions

TO-3PN

(Dimensions in Millimeters)

